





# **Phase Control Thyristor**

**Preliminary Information** 

DS5933-3.0 August 2010 (LN 27489)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR3220A65* DCR3220A60 DCR3220A55	6500 6000 5500	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM}  t_p = 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} &= \\ V_{DRM}  \&  V_{RRM} + 100V \\ respectively \end{split}$

Lower voltage grades available. \*6200V @ -40°C, 6500V @ 0°C

#### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

# DCR3220A65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

6500V
3310A
44200A
2000V/µs
200Α/μs

\* Higher dV/dt selections available

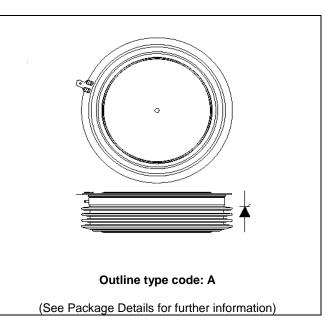


Fig. 1 Package outline





# **CURRENT RATINGS**

# $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	3220	А
I <sub>T(RMS)</sub>	RMS value	-	5058	А
Ιτ	Continuous (direct) on-state current	-	4655	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	43.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	9.25	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.00603	°C/W
		Single side cooled	Anode DC	-	0.01024	°C/W
			Cathode DC	-	0.01467	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 83.0kN	Double side	-	0.001	°C/W
		(with mounting compound)	Single side	-	0.002	°C/W
T <sub>vj</sub>	Virtual junction temperature	Blocking V <sub>DRM</sub> / V <sub>RRM</sub>	•	-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
Fm	Clamping force			74.0	91.0	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	500	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
$V_{T(TO)}$	Threshold voltage – Low level	500 to 1900A at T <sub>case</sub> = 125°	С	-	1.01	V
	Threshold voltage – High level	1900 to 6000A at T <sub>case</sub> = 125	°C	-	1.08	V
r <sub>T</sub>	On-state slope resistance – Low level	500A to 1900A at T <sub>case</sub> = 125	5°C	-	0.3	mΩ
	On-state slope resistance – High level	1600A to 6000A at T <sub>case</sub> = 125°C		-	0.2643	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$I_T = 3000A$ , $T_j = 125$ °C, $V_R = 200V$ , $dI/dt = 1A/\mu s$ ,			500	μs
		dV <sub>DR</sub> /dt = 20V/μs linear				
Qs	Stored charge	- I <sub>T</sub> = 3000A, T <sub>j</sub> = 125°C, dI/dt – 1A/μs, V <sub>Rpeak</sub> ~3900V, V <sub>R</sub> ~ 2600V		3830	6430	μC
I <sub>RR</sub>	Reverse recovery current			45	60	А
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I <sub>H</sub>	Holding current	$T_j = 25$ °C, $R_{G-K} = \infty$ , $I_{TM} = 500$ A, $I_T = 5$ A		-	300	mA





### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	300	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

# **CURVES**

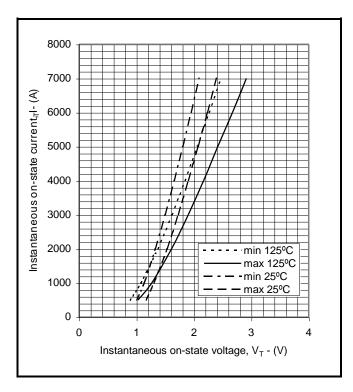


Fig.2 Maximum & minimum on-state characteristics

**V<sub>TM</sub> EQUATION** 

Where A = -0.645429B = 0.3001939

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$ 

C = 0.000276

D = -0.01259

these values are valid for  $T_j = 125$ °C for  $I_T 500$ A to 6000A



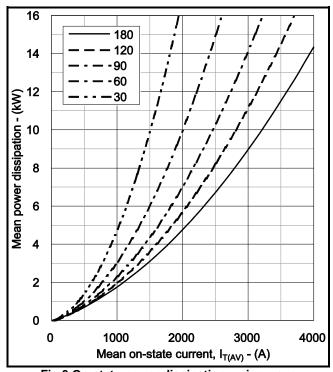


Fig.3 On-state power dissipation - sine wave

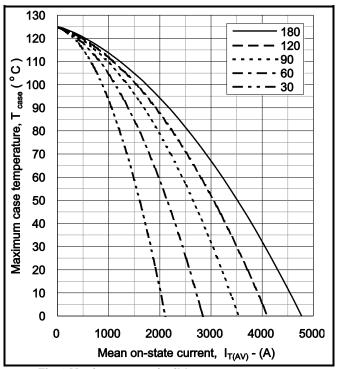


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

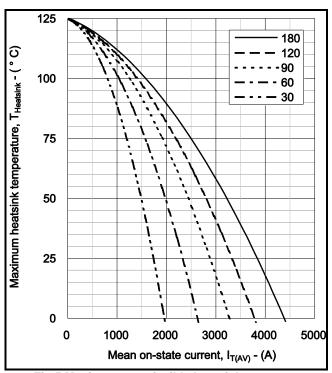


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

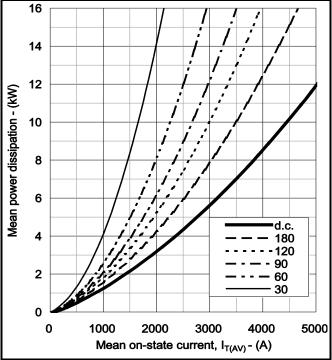


Fig.6 On-state power dissipation - rectangular wave



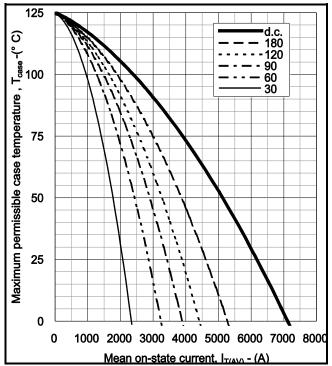


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

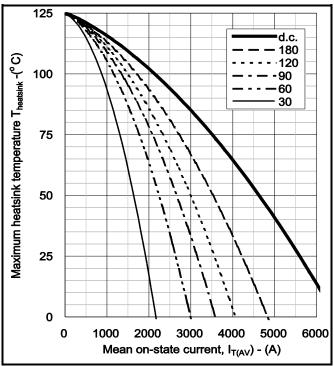
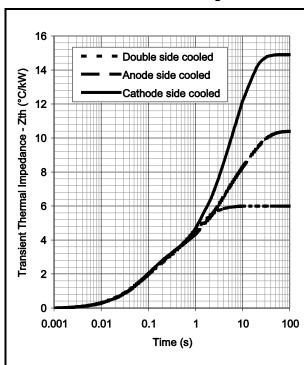


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	3.01541	1.048955	0.983519	0.983519
Double side cooled	T <sub>i</sub> (s)	0.703874	1.904794	0.059	0.059
Anode side cooled	R <sub>i</sub> (°C/kW)	3.156003	4.092806	1.556555	1.623962
	T <sub>i</sub> (s)	2.69023	13.79162	0.059	0.205916
Cathode side cooled	R <sub>i</sub> (°C/kW)	7.077369	3.483481	1.745839	2.634274
Catriode side cooled	T. (s)	6 648601	8 436484	1 762119	0.08069

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(T/T_i))]$$

#### $\Delta R_{th(j-c)}$ Conduction

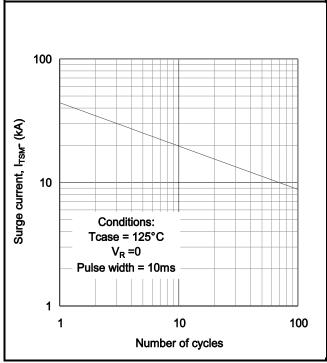
Tables show the increments of thermal resistance  $R_{\text{th(j-c)}}$  when the device operates at conduction angles other than d.c.

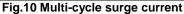
Double side cooling			Anode Side Cooling		
	$\Delta Z_{th}$ (z)			$\Delta Z_t$	<sub>h</sub> (z)
θ°	sine.	rect.	θ°	sine.	rect.
180	0.44	0.31	180	0.42	0.30
120	0.49	0.43	120	0.47	0.41
90	0.55	0.49	90	0.52	0.46
60	0.60	0.55	60	0.57	0.52
30	0.64	0.61	30	0.61	0.58
15	0.66	0.64	15	0.62	0.61

Cath	node Sided Cooling					
	$\Delta Z_{th}(z)$					
θ°	sine.	rect.				
180	0.42	0.30				
120	0.47	0.41				
90	0.52	0.46				
60	0.57	0.52				
30	0.60	0.58				
15	0.62	0.60				

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)







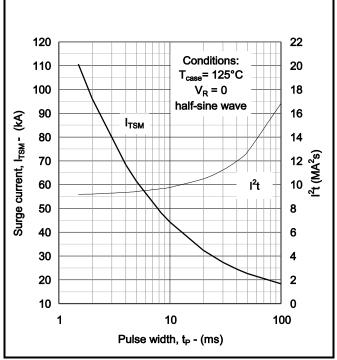


Fig.11 Single-cycle surge current

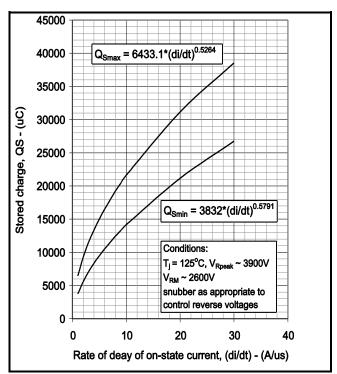


Fig.12 Stored charge

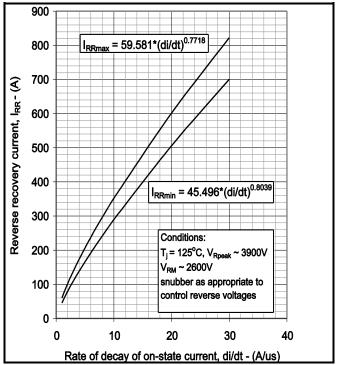


Fig.13 Reverse recovery current

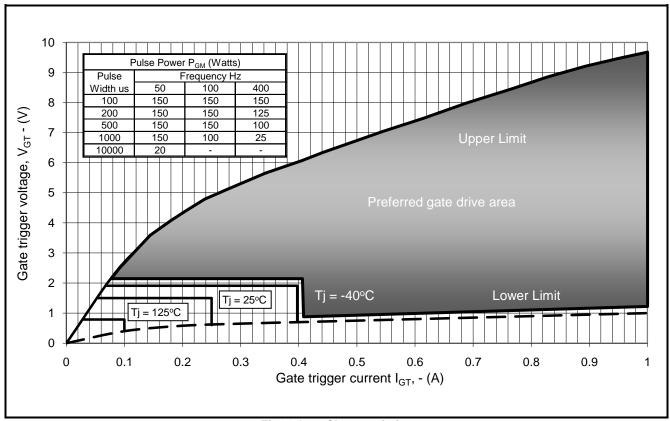


Fig14 Gate Characteristics

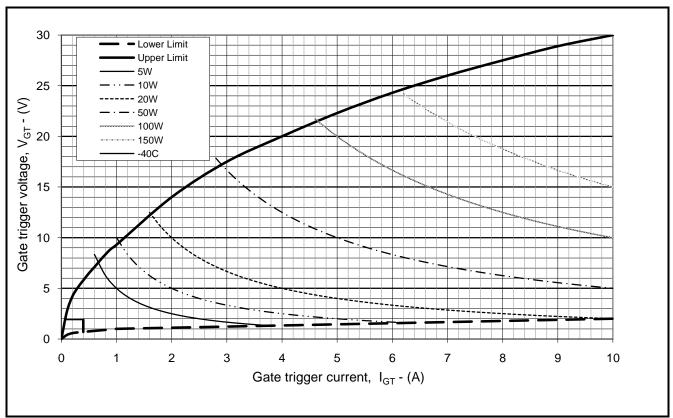


Fig. 15 Gate characteristics



### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

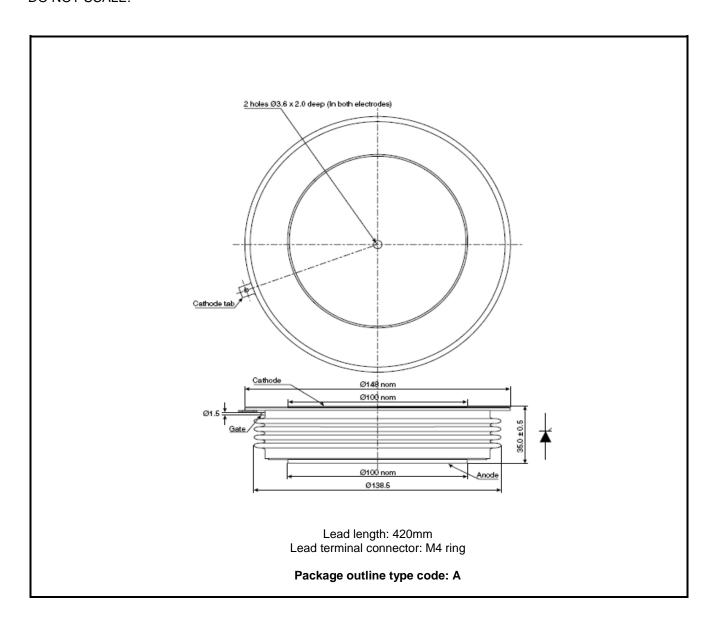


Fig.16 Package outline





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